

# FM24C04D 2-Wire Serial EEPROM With Unique ID and Security Sector

Data Sheet

Sep.2023



INFORMATION IN THIS DOCUMENT IS INTENDED AS A REFERENCE TO ASSIST OUR CUSTOMERS IN THE SELECTION OF SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD PRODUCT BEST SUITED TO THE CUSTOMER'S APPLICATION AND SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD DOES NOT GUARANTEE THE AUTHENTICITY AND INTEGRITY OF THE INFORMATION.

INFORMATION DO NOT CONVEY ANY LICENSE UNDER ANY INTELLECTUAL PROPERTY RIGHTS, OR ANY OTHER RIGHTS, BELONGING TO SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD OR A THIRD PARTY.

WHEN USING THE INFORMATION CONTAINED IN THIS DOCUMENTS, PLEASE BE SURE TO EVALUATE ALL INFORMATION AS A TOTAL SYSTEM BEFORE MAKING A FINAL DECISION ON THE APPLICABILITY OF THE INFORMATION AND PRODUCTS. PURCHASERS ARE SOLELY RESPONSIBLE FOR THE CHOICE, SELECTION AND USE OF THE SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD PRODUCTS AND SERVICES DESCRIBED HEREIN, AND SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD ASSUMES NO LIABILITY WHATSOEVER RELATING TO THE CHOICE, SELECTION OR USE OF THE SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD ASSUMES NO LIABILITY WHATSOEVER RELATING TO THE CHOICE, SELECTION OR USE OF THE SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD PRODUCTS AND SERVICES DESCRIBED HEREIN. UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

FUTURE ROUTINE REVISIONS WILL OCCUR WHEN APPROPRIATE, WITHOUT NOTICE. CONTACT SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD SALES OFFICE TO OBTAIN THE LATEST SPECIFICATIONS AND BEFORE PLACING YOUR PRODUCT ORDER. PLEASE ALSO PAY ATTENTION TO INFORMATION PUBLISHED BY SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD BY VARIOUS MEANS, INCLUDING SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD HOME PAGE (HTTP://WWW.FMSH.COM/).

PLEASE CONTACT SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD LOCAL SALES OFFICE FOR THE SPECIFICATION REGARDING THE INFORMATION IN THIS DOCUMENT OR SHANGHAI FUDAN MICROELECTRONICS GROUP CO., LTD PRODUCTS.

#### Trademarks

Shanghai Fudan Microelectronics Group Co., Ltd name and logo, the "复旦" logo are trademarks or registered trademarks of Shanghai Fudan Microelectronics Group Co., Ltd or its subsidiaries in China. Shanghai Fudan Microelectronics Group Co., Ltd, Printed in the China, All Rights Reserved.

## Description

The FM24C04D provides 4096 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 512 words of 8 bits each, with 128-bit UID and 16-byte Security Sector. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operations are essential.

# Features

- Low Operation Voltage: Vcc = 1.7V to 5.5V
- Internally Organized: 512 x 8
- 2-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bi-directional Data Transfer Protocol
- 1MHz (2.5V~5.5V) and 400 kHz (1.7V) Compatibility
- Write Protect Pin for Hardware Data Protection
- 16-Byte Page Write Modes (Partial Page Writes are Allowed)
- Lockable 16-Byte Security Sector
- 128-Bit Unique ID for each device
- Self-timed Write Cycle (5 ms max)
- High-reliability
  - Endurance: 1,000,000 Write Cycles
    Data Retention: 40 Years (55°C)
- PDIP8 (RoHS Compliant)
- SOP8, TSSOP8, TSOT23-5L and TDFN8 Packages (RoHS Compliant and Halogen-free)
- Wafer Sales: available in Wafer Form

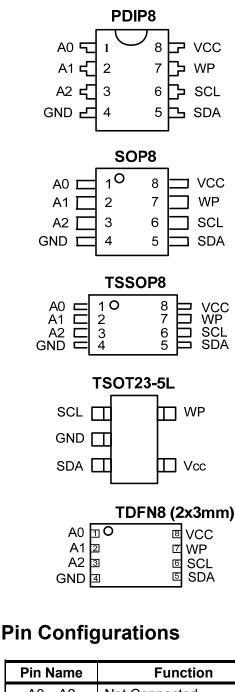
# **Absolute Maximum Ratings**

Ambient Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground	-0.5V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

\*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

上海复旦微电子集团股份有限公司

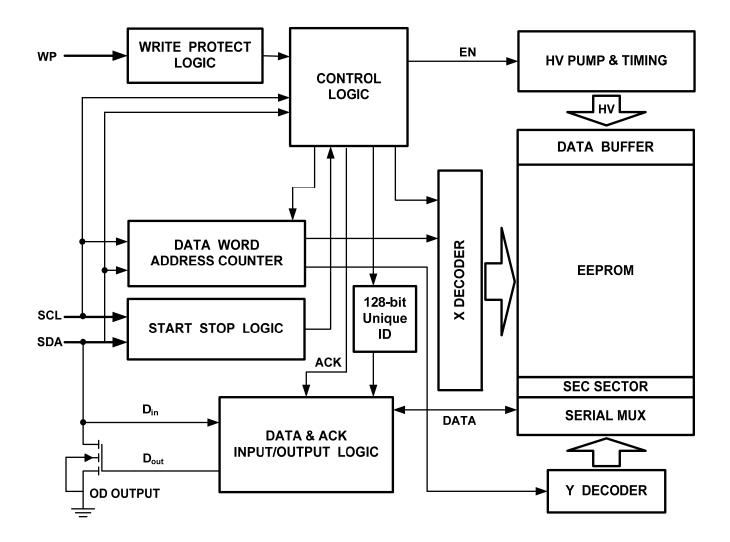
# Packaging Type



Pin Name	Function
A0~A2	Not Connected
SDA	Serial Data Input/Output
SCL	Serial Clock Input
WP	Write Protect
Vcc	Power Supply
GND	Ground

复旦微电子

## Figure 1. Block Diagram



**後** 复旦微电子



# Pin Description

**SERIAL CLOCK (SCL):** The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

**SERIAL DATA (SDA):** The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

**DEVICE/PAGE ADDRESSES:** A total of one device may be addressed on a single bus system.

WRITE PROTECT (WP): The FM24C04D has a

Write Protect pin that provides hardware data protection. The WP pin allows normal write operations when connected to ground (GND). When the Write Protect pin is connected to VCC, all write operations to the memory are inhibited. If the pin is left floating, the WP pin will be internally pulled down to GND if the capacitive coupling to the circuit board Vcc plane is <3pF. If coupling is >3pF, FMSH recommends connecting the WP to GND. Switching WP to VCC prior to a write operation creates a software write protected function.

## Write Protect Description

WP Pin Status	Part of the Array Protected
WP=V <sub>CC</sub>	Full Array
WP=GND	Normal Read/Write Operations

When the WP pin is connected to the  $V_{CC}$ , write operation to memory area is inhibited. When the WP pin is connected to GND or set in open, the write protect is invalid, and write operation in all memory area is available.

Write-protect condition: The WP pin must be connected to VCC from start condition in the write operation (byte write, page write) until stop condition (refer to Figure 10).

**Non-write-protect condition:** The WP pin must be connected to GND from start condition in the write operation (byte write, page write) until stop condition (refer to Figure 11).

In not using the write protect, connect the WP pin to GND or set it open. The write protect is valid in the range of operation power supply voltage. If the WP pin changes during this time, the address data being written at this time is not guaranteed. Regarding the timing of write protect, refer to Figure 3.

# Memory Organization

**FM24C04D, 4K SERIAL EEPROM:** Internally organized with 64 pages of 16 bytes each, the 4K requires an 9-bit data word address for random word addressing.

**Security Sector:** The FM24C04D offers 16-byte Security Sectors which can be written and (later) permanently locked in Read-only mode. These registers may be used by the system manufacturers to store security and other important information separately from the main memory array.

**Unique ID:** The FM24C04D utilizes a separate memory block containing a factory programmed 128-bit unique ID. Access to this memory location is obtained by beginning the device address word with a '1011'(Bh) sequence.

Device Address	WORD Address	Memory Organization
1010 00xx <sup>1</sup>	XXXX XXXX <sup>2</sup>	Data Memory (32 X 16B)
1011 00xx <sup>3</sup>	00xx xxxx <sup>4</sup>	Security Sector (1 X 16B)
1011 00x1 <sup>5</sup>	10xx xxxx <sup>6</sup>	Unique ID (1 X 16B)

Note:

1. The seventh bit are memory page address bits (P0) ,and the eighth bit is the read/write operation select bit.

2. Address bits P0 and A<7:4> define page address and A<3:0> define byte address.

3. The seventh bit is don't care, and the eighth bit is the read/write operation select bit.

4. Address bits A<7:6> must be '00', A<3:0> define byte address, other bits are don't care.

5. The seventh bit is don't care, and the eighth bit is the read/write operation select bit which must be '1'.

6. Address bits A<7:6> must be '10', A<3:0> define byte address, other bits are don't care.

上海复旦微电子集团股份有限公司

Data Sheet 5



# **Pin Capacitance**

SYMBOL	PARAMETER	CONDITIONS	Max	Units
CIN <sup>1</sup>	Input Capacitance	$V_{IN} = 0V, f = 1MHz$	6	pF
Cout <sup>1</sup>	Output Capacitance	$V_{OUT} = 0V, f = 1MHz$	8	pF

Note: 1. This parameter is characterized and is not 100% tested.

# **DC Characteristics**

Applicable over recommended operating range from:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.7V$  to +5.5V, (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
Vcc	Supply Voltage		1.7		5.5	V
Icc1	Supply Current	V <sub>CC</sub> = 5.0V, Read at 400KHz		0.4	1.0	mA
Icc2	Supply Current	V <sub>CC</sub> = 5.0V, Write at 400KHz		2.0	3.0	mA
ISB1	Standby Current	$V_{CC}$ = 1.7V, $V_{IN}$ = $V_{CC}/V_{SS}$			1.0	μA
SB2	Standby Current	$V_{CC}$ = 5.5V, $V_{IN}$ = $V_{CC}/V_{SS}$			6.0	μA
ILI	Input Leakage Current	V <sub>IN</sub> = V <sub>CC</sub> /V <sub>SS</sub>		0.1	3.0	μA
Ilo	Output Leakage Current	Vout = Vcc/Vss		0.05	3.0	μA
VIL <sup>1</sup>	Input Low Level		-0.6		Vcc x 0.3	V
VIH <sup>1</sup>	Input High Level		Vcc x 0.7		V <sub>CC</sub> + 0.5	V
Vol2	Output Low Level 2	$V_{CC}$ = 3.0V, $I_{OL}$ = 2.1 mA			0.4	V
Vol1	Output Low Level 1	V <sub>CC</sub> =1.7V, I <sub>OL</sub> = 0.15 mA			0.2	V

Note: 1.  $V_{IL}$  min and  $V_{IH}$  max are reference only and are not tested.

# **AC Characteristics**

#### 400 kHz AC characteristics

Recommended operating conditions:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.7V$  to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
fscl	Clock Frequency, SCL		400	kHz
t <sub>LOW</sub>	Clock Pulse Width Low	1.3		μs
tнigн	Clock Pulse Width High	0.6		μs
t <sub>l</sub> 1	Noise Suppression Time		80	ns
taa	Clock Low to Data Out Valid	0.1	0.9	μs
tbuf <sup>1</sup>	Time the bus must be free before a new transmission can Start	1.3		μs
thd.sta	Start Hold Time	0.6		μs
tsu.sta	Start Setup Time	0.6		μs
thd.dat	Data In Hold Time	0		μs
tsu.dat	Data In Setup Time	100		ns
t <sub>R</sub>	Inputs Rise Time <sup>1</sup>		300	ns
t⊨	Inputs Fall Time <sup>1</sup>		300	ns
tsu.sто	Stop Setup Time	0.6		μs
t <sub>DH</sub>	Data Out Hold Time	100		ns
tws₁	WP setup time	1		us
t <sub>WH1</sub>	WP hold time	1		us
tws2	WP release setup time	1		us
twH2	WP release hold time	1		us
twr	Write Cycle Time		5	ms
Endurance <sup>1</sup>	3.3V, 25°C, Page Mode	1,000	0,000	Write Cycles

#### 1 MHz AC characteristics

Recommended operating conditions:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +2.5V$  to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
fscl	Clock Frequency, SCL		1	MHz
tLOW	Clock Pulse Width Low	500		ns
tніgн	Clock Pulse Width High	320		ns
tı 1	Noise Suppression Time		80	ns
taa	Clock Low to Data Out Valid		450	ns
tbuf <sup>1</sup>	Time the bus must be free before a new transmission can Start	500		ns
t <sub>hd.sta</sub>	Start Hold Time	250		ns
tsu.sta	Start Setup Time	250		ns
t <sub>HD.DAT</sub>	Data In Hold Time	0		ns
tsu.dat	Data In Setup Time	50		ns
t <sub>R</sub>	Inputs Rise Time <sup>1</sup>		120	ns
t⊧	Inputs Fall Time <sup>1</sup>		120	ns
tsu.sto	Stop Setup Time	250		ns

上海复旦微电子集团股份有限公司 Shanghai Fudan Microelectronics Group Company Limited 复旦微电子

	Shanghai Fudan Microelectronics Group Company Limited				
t <sub>DH</sub>	Data Out Hold Time	100		ns	
t <sub>ws1</sub>	WP setup time	1		us	
t <sub>WH1</sub>	WP hold time	1		us	
t <sub>WS2</sub>	WP release setup time	1		us	
t <sub>WH2</sub>	WP release hold time	1		us	
twR	Write Cycle Time		5	ms	
Endurance <sup>1</sup>	3.3V, 25°C, Page Mode	1,000,000		Write Cycles	

Notes: 1. This parameter is characterized and is not 100% tested.

2. AC measurement conditions:

RL (connects to V<sub>CC</sub>): 1.3  $k\Omega$ Input pulse voltages: 0.3 Vcc to 0.7 Vcc Input rise and fall times: ≤ 50 ns Input and output timing reference voltages: 0.5  $V_{\text{CC}}$ 

## **Device Operation**

**CLOCK and DATA TRANSITIONS:** The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Figure 4). Data changes during SCL high periods will indicate a start or stop condition as defined below.

**START CONDITION:** A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Figure 5).

**STOP CONDITION:** A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Figure 5).

**ACKNOWLEDGE:** All address and data words are serially transmitted to and from the EEPROM in 8-bit

words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

复旦微电子

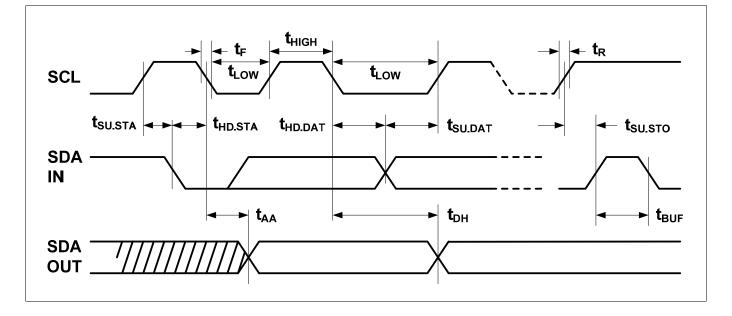
**STANDBY MODE:** The FM24C04D features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the stop bit and the completion of any internal operations.

**Memory RESET:** After an interruption in protocol, power loss or system reset, any 2-wire part can be reset in following these steps:

- 1. Clock up to 9 Cycles,
- 2. Look for SDA high in each cycle while SCL is high and then,
- 3. Create a start condition as SDA is high.

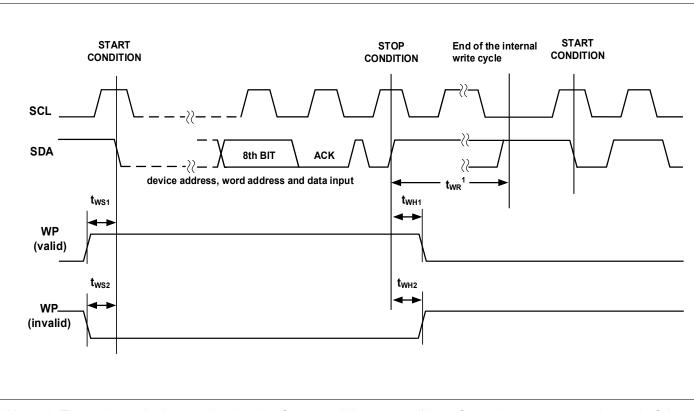
# **Bus Timing**







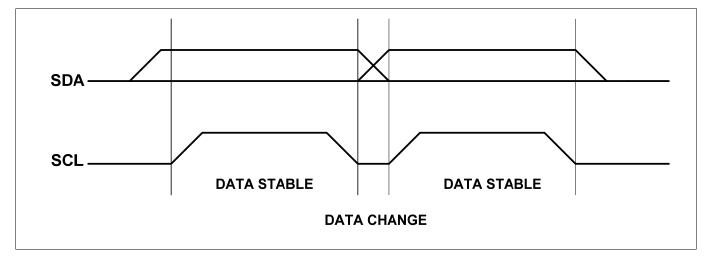
# Write Cycle Timing



### Figure 3. SCL: Serial Clock, SDA: Serial Data I/O

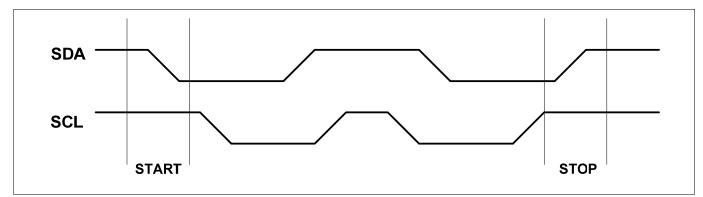
Note: 1. The write cycle time twR is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

Figure 4. Data Validity

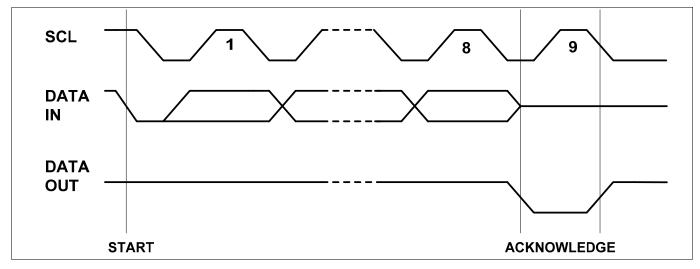




### Figure 5. Start and Stop Definition



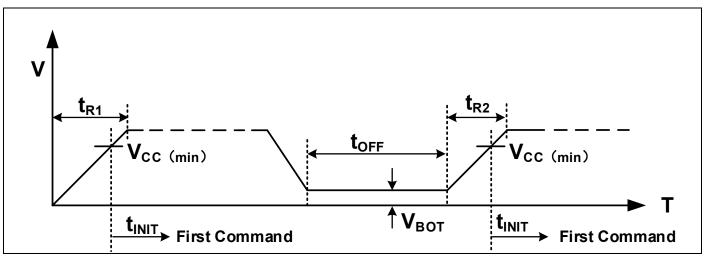






# **Power-up Timing**





Symbol	Parameter	Test Condition	Min	Max	Units
t <sub>R1</sub>	Power on time from 0V			20	ms
t <sub>R2</sub>	Power on time from VBOT	V <sub>BOT</sub> ≪0.2V		5	ms
toff	power cycle off time		50		ms
<b>t</b> <sub>INIT</sub>	Time from power on to first command		100		us
VBOT	Power Off threshold for the next power on cycle	No ringback above V <sub>POFF</sub>		0.2	V

Note: VCC must rise monotonically without ringback.

# **Device Addressing**

#### Data Memory Access:

The FM24C04D device requires an 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Table 1~Table 2).

The device address word consists of a mandatory '1010' sequence for the first four most significant bits and the fifth to seventh bits are memory page address bits as shown in Table 1~Table 2.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the chip will return to a standby state.

**Unique ID Access:** The FM24C04D utilizes a separate memory block containing a factory programmed 128-bit unique ID. Access to this memory location is obtained by beginning the device address word with a '1011'(Bh) sequence (refer to Table 1~Table 2). The behavior of the next three bits remains the same as during a standard memory addressing sequence.

The eighth bit of the device address needs be set to a

one to read the Serial Number. Writing or altering the 128-bit unique ID is not possible.

😫 复旦微电子

For more details on accessing this special feature, See Read Operations on page 15.

**Security Sector Access:** The FM24C04D offers 16-byte Security Sector which can be written and (later) permanently locked in Read-only mode. Access to this memory location is obtained by beginning the device address word with a '1011'(Bh) sequence (refer to Table 1~Table 2). The behavior of the next three bits remains the same as during a standard memory addressing sequence.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

For more details on accessing this special feature, See Write Operations and Read Operations on page 15.

**NOISE PROTECTION:** Special internal circuitry placed on the SDA and SCL pins prevent small noise spikes from activating the device.

**DATA SECURITY:** The Device has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at  $V_{CC}$ .

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	1	0	1	0	0	0	P0	R/W
Security Sector	1	0	1	1	0	0	х	R/W
Security Sector Lock Bit	1	0	1	1	0	0	х	R/W
Unique ID Number	1	0	1	1	0	0	х	1
	MSB							LSB

#### Table 1. Device Address

#### Table 2.Word Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	A7	A6	A5	A4	A3	A2	A1	A0
Security Sector	0	0	х	х	A3	A2	A1	A0
Security Sector Lock Bit	х	1	х	х	х	х	х	х
Unique ID Number	1	0	х	х	0	0	0	0
	MSB	•		•	•		•	LSB

**NOTE: x** = **Don**`t care bit.

## Write Operations

**BYTE WRITE:** A write operation requires two 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle, twR, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (refer to Figure 8).

**PAGE WRITE:** The 4K EEPROM is capable of 16-byte page writes. A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (refer to Figure 9).

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten. **ACKNOWLEDGE POLLING:** Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

复旦微电子

**WRITE SECURITY SECTOR:** Write the Security Sector is similar to the page write but requires use of device address, and the special word address seen in Table 1~Table 2 on page 13. Address bits A<7:6> which must be equal to '00b'. Lower address bits A<3:0> define the byte address inside the Security Sector (refer to Figure 15).And other address bits are don't care.

If the Security Sector is locked, the data bytes transferred during the Write Security Sector operation are not acknowledged (NoAck).

**LOCK SECURITY SECTOR:** Lock the Security Sector is similar to the byte write but requires use of device address, and special word address seen in Table 1~Table 2 on page 13. The word address bits A<7:6> must be 'x1b', all other word address bits are don't care. The data byte must be equal to the binary value xxxx xx1x, where x is don't care (see Figure 17).

If the Security Sector is locked, the data bytes transferred during the Lock Security Sector operation are not acknowledged (NoAck).

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one.

**CURRENT ADDRESS READ:** The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (see Figure 12).

**RANDOM READ:** A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (see Figure 13).

**SEQUENTIAL READ:** Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 14 )

**UNIQUE ID READ:** Reading the serial number is similar to the sequential read but requires use of the device address, a dummy write, and the use of specific word address seen in Table 1~Table 2 on page 13. Address bits A<7:6> which must be equal to '10b'. Lower address bits A<3:0> define the byte address inside the UID. And other address bits are

don't care. If the application desires to read the first byte of the UID, the lower address bits A<3:0> would need to be '0000b'.

🖐 复旦微电子

When the end of the 128-bit UID number is reached (16 bytes of data), the data word address will roll-over back to the beginning of the 128-bit UID number. The Unique ID Read operation is terminated when the microcontroller does not respond with a zero (ACK) and instead issues a Stop condition (see Figure 19).

**READ SECURITY SECTOR:** Read the Security Sector is similar to the random read but requires use of device address, a dummy write, and the use of specific word address seen in Table 1~Table 2 on page 13. The higher address bits are don't care except for address bits A<7:6>, which must be equal to '00b'. The lower address bits A<3:0> define the byte address inside the Security Sector.

The internal byte address is automatically incremented to the next byte address after each byte of data is clocked out. When the last byte (0Fh) is reached, it will roll over to 00h, the first byte of the Security Sector, and continue to increment. (see Figure 16).

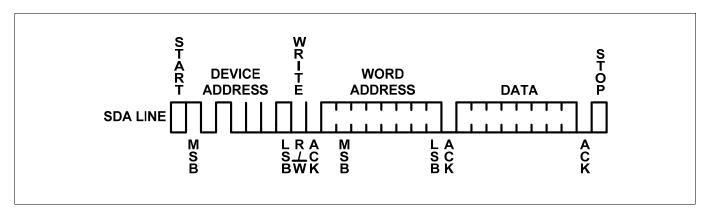
**READ LOCK STATUS:** There are two ways to check the lock status of the Security Sector.

1. The first way is initiated by a Security Sector Write, the EEPROM will acknowledge if the Security Sector is unlocked, while it will not acknowledge if the Security Sector is locked.

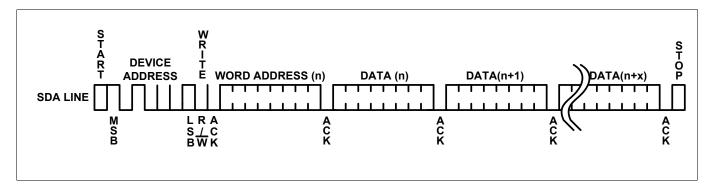
Once the acknowledge bit is read, it is recommended to generate a Start condition followed by a Stop condition, so that:

- Start: the truncated command is not executed because the Start condition resets the device internal logic
- Stop: the device is then set back into Standby mode by the Stop condition.

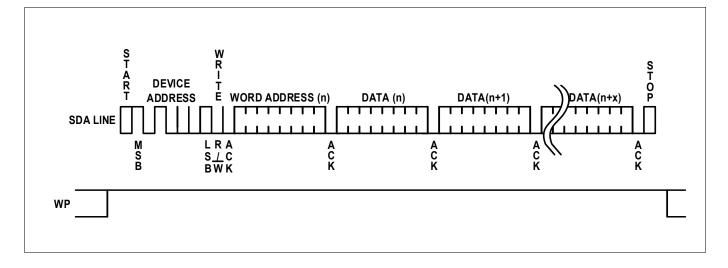
2. The second way is initiated by a Lock Status Read. Lock Status Read is similar to the random read but requires use of device address seen in Table 1 on page 13, a dummy write, and the use of specific word address. The address bits A<7:6> must be 'x1b', all other address bits are Don't Care. The Lock bit is the BIT1 of the byte read on SDA. It is at "1" when the lock is active and at "0" when the lock is not active. The same data is shifted out repeatedly until the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 18 ). Figure 8. Byte Write



## Figure 9. Page Write







**巡**复旦微电子

🖐 复旦微电子



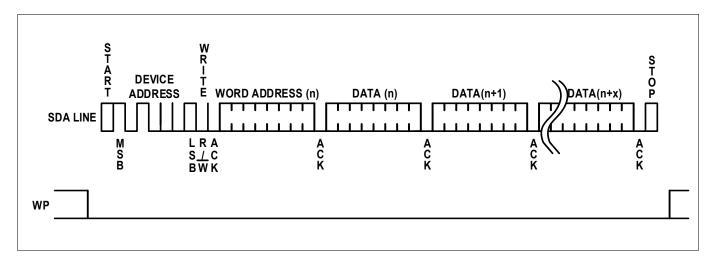


Figure 12. Current Address Read

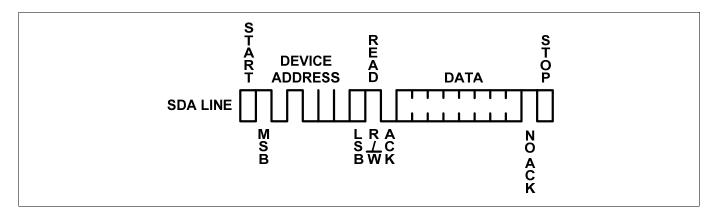
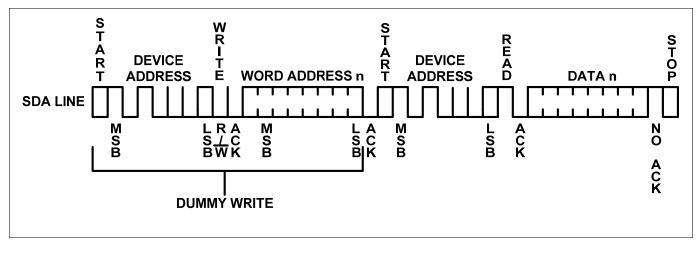
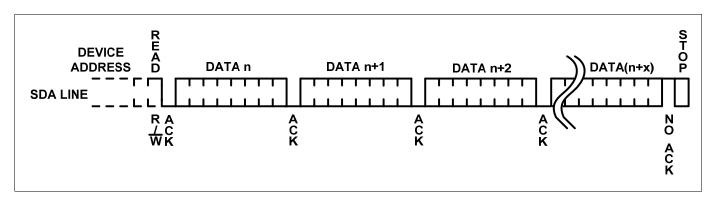


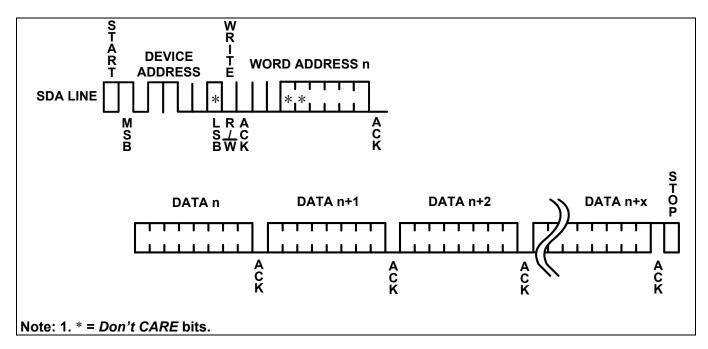
Figure 13. Random Read





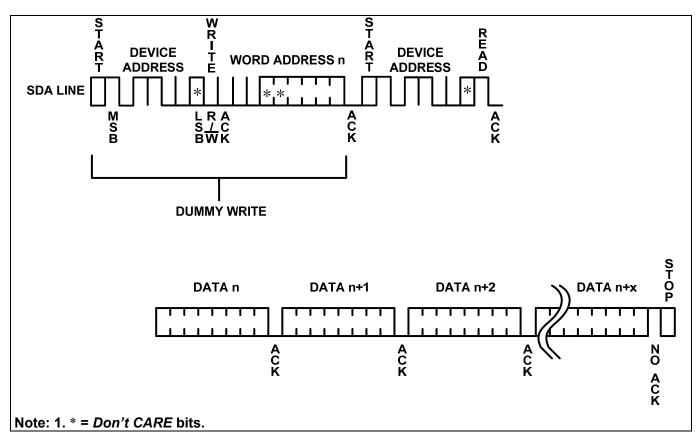




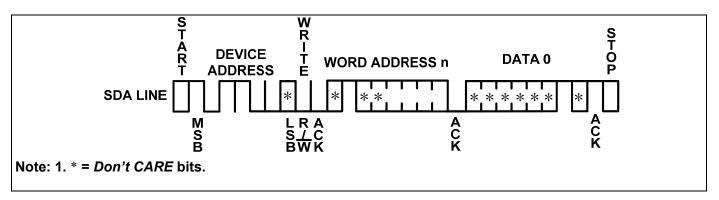


**》**复旦微电子





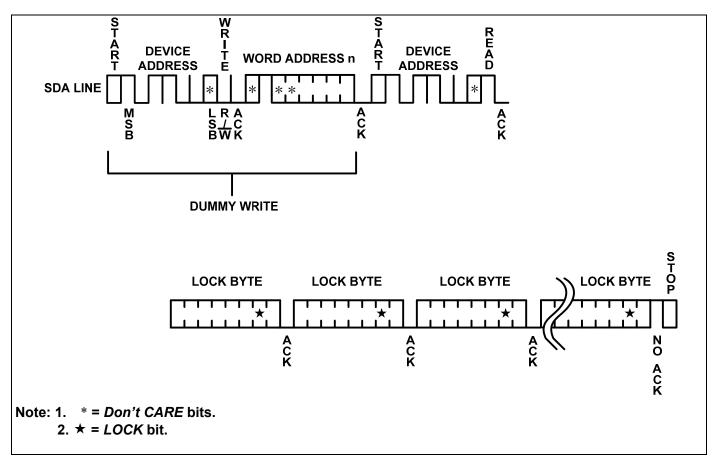




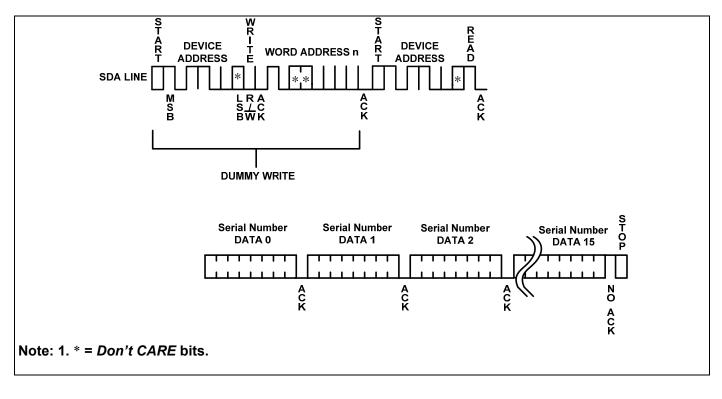
**》**复旦微电子

# **》**。复旦微电子

## Figure 18. Read Lock Status



## Figure 19. Read Unique ID





# **Ordering Information**

	FM	24	ŀC	04	D -P	Ρ	-C	-H
Company Prefix						_		
FM = Shanghai Fudan Microelectronics Group Co.,Ito	k							
Product Family								
24C = 2-Wire Serial EEPROM								
Product Density								
04 = 4K-bit								
Device Type								
D = with 128-bit Unique ID with 16-byte Security Sector								
Package Type <sup>1</sup>								
PD = 8-pin PDIP								
SO = 8-pin SOP								
TS = 8-pin TSSOP DN = 8-pin TDFN (2X3mm) $^{2}$								
ST = 5-pin TSOT23								
Product Carrier								
U = Tube								
T = Tape and Reel								
HSF ID Code <sup>3</sup>								

Blank or R = RoHS Compliant G = RoHS Compliant, Halogen-free, Antimony-free

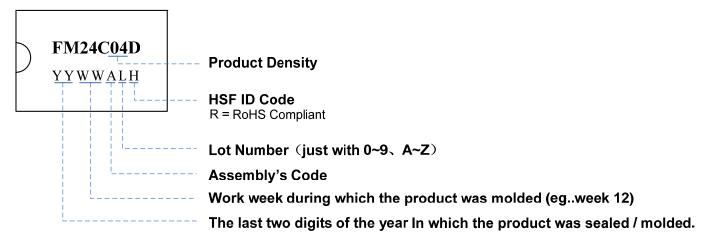
Note:

- 1. For DN package, MSL1 package are available, for detail please contact local sales office.
- For Thinner package please contact local sales office.
   For PD package: R class only.
- For SO, TS, DN and ST package: G class only.

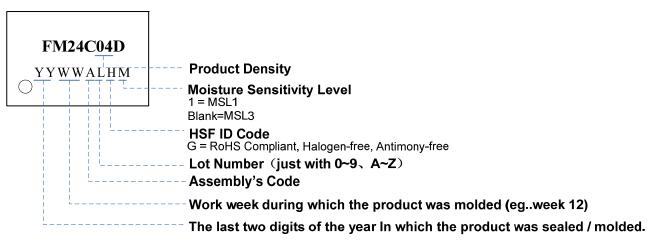


# **Part Marking Scheme**

#### PDIP8



### SOP8

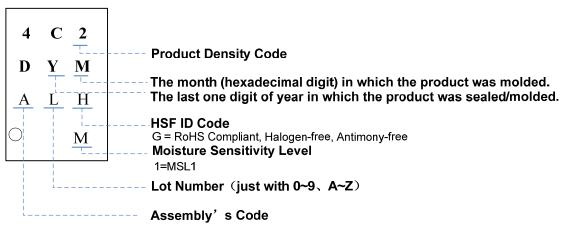


### TSSOP8

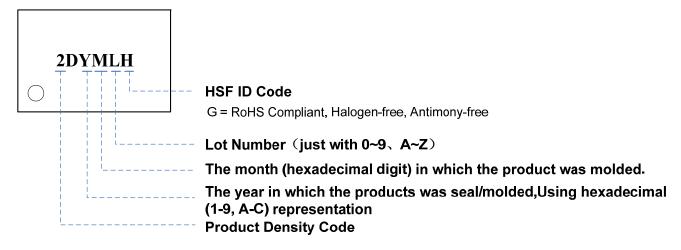
FM24C04D	
YYWWALHM	Product Density
	<b>Moisture Sensitivity Level</b> 1=MSL1 Blank=MSL3
	G = RoHS Compliant, Halogen-free, Antimony-free Lot Number (just with 0~9、A~Z)
	Assembly's Code
	Work week during which the product was molded (egweek 12)
L	The last two digits of the year In which the product was sealed / molded.

# 👋 🖉 复旦微电子

## TDFN8 (2x3mm)

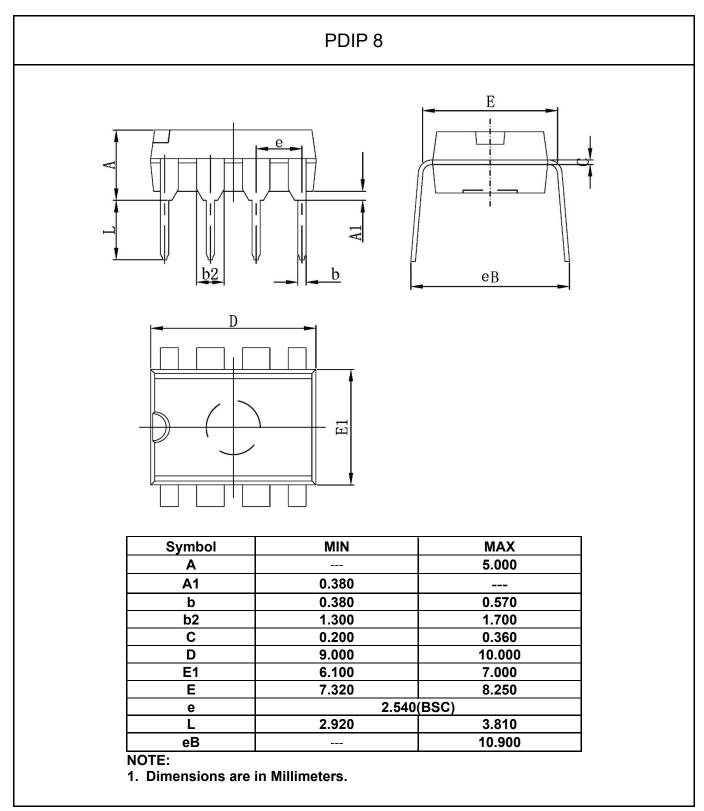


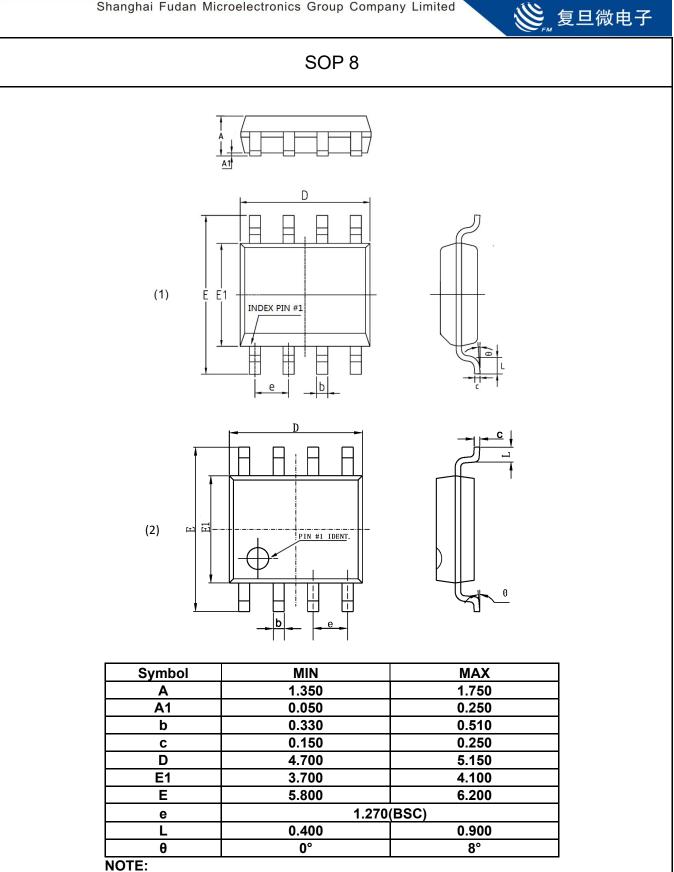
### TSOT23-5L





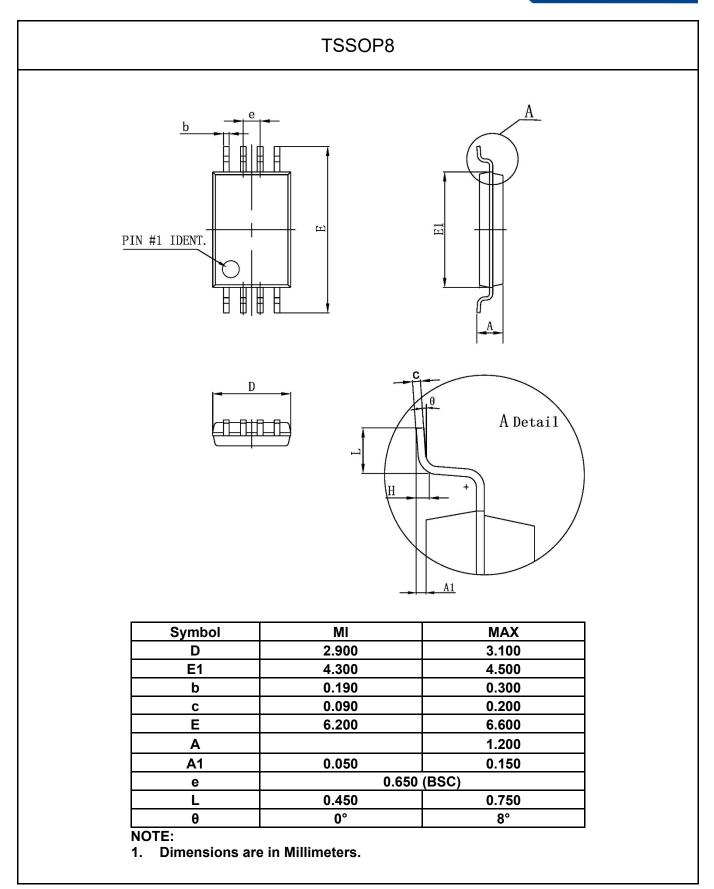
# **Packaging Information**



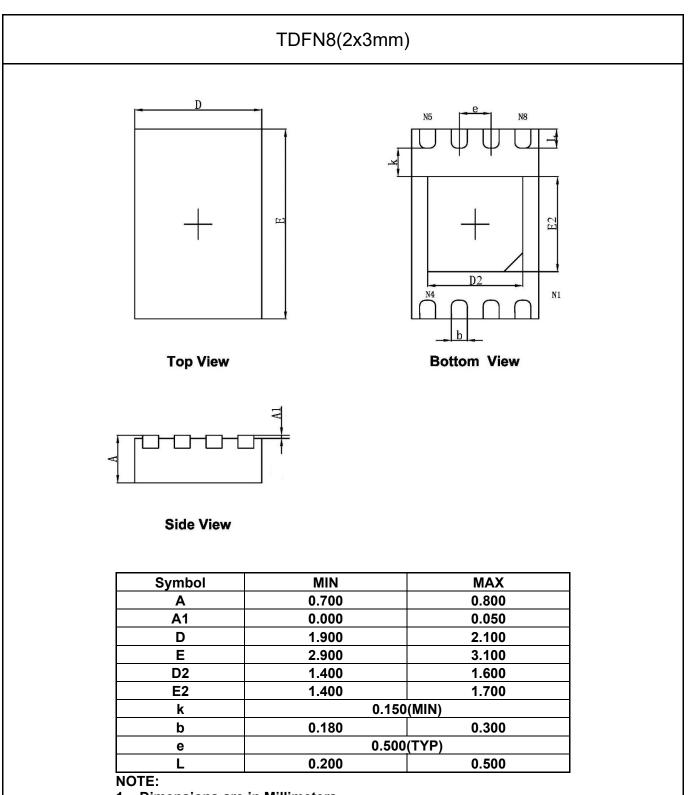


1. Dimensions are in Millimeters.

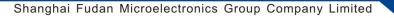








1. Dimensions are in Millimeters.



TSOT23-5L D b 0.25 El ы е e1 MIN MAX Symbol 0.700 0.900 Α **A1** 0.000 0.100 0.350 b 0.500 0.200 0.080 С D 2.820 3.020 E1 1.600 1.700 Ε 2.650 2.950 0.950(BSC) е 1.900(BSC) e1

0.300

**0°** 

NOTE:

L

θ

1. Dimensions are in Millimeters.

上海复旦微电子集团股份有限公司 Shanghai Fudan Microelectronics Group Company Limited 0.600

**8°** 

**後** 复旦微电子



# **Revision History**

Version	Publication date	Pages	Revise Description	
1.0	Sep. 2014	28	Initial document Release.	
1.1	Dec.2014	28	<ol> <li>Updated Package pin configurations: Pin name changed from 'NC' to 'A2~A0'.</li> <li>Name of data memory page address bit in device address changed from 'A8' to 'P0'.</li> <li>Updated the chapters of packaging type, Ordering information, Part marking scheme and packaging information.</li> </ol>	
1.2	Dec. 2015	28	Updated packaging information.	
1.3	Aug. 2020	28	Updated packaging information.	
1.4	May. 2021	28	Corrected some typo.	
1.5	Apr. 2022	29	Added power up timing.	
1.6	Feb.2023	30	<ol> <li>Added t<sub>WS1</sub>/ t<sub>WH1</sub>/ t<sub>WS2</sub>/ t<sub>WH2</sub> AC parameter.</li> <li>Updated Write Protect description.</li> </ol>	
1.7	Jun.2023	30	<ol> <li>Corrected the typo.</li> <li>Updated packaging information.</li> </ol>	
1.8	Sep.2023	30	1.Updated packaging information.	



# Sales and Service

**Shanghai Fudan Microelectronics Group Co. Shanghai Fudan Microelectronics Group Co., Ltd.** Address: Bldg No. 4, 127 Guotai Rd, Shanghai City China. Postcode: 200433 Tel: (86-021) 6565 5050 Fax: (86-021) 6565 9115

#### Shanghai Fudan Microelectronics (HK) Co., Ltd.

Address: Unit 506, 5/F., East Ocean Centre, 98 Granville Road, Tsimshatsui East, Kowloon, Hong Kong Tel: (852) 2116 3288 2116 3338 Fax: (852) 2116 0882

#### **Beijing Office**

Address: Room 423, Bldg B, Gehua Building, 1 QingLong Hutong, Dongzhimen Alley north Street, Dongcheng District, Beijing City, China. Postcode: 100007 Tel: (86-010) 8418 6608 Fax: (86-010) 8418 6211

#### **Shenzhen Office**

Address: Room.2306-2308, Building A7, Chuangzhi Cloud City, Liuxian Avenue, Xili Street, Nanshan District, Shenzhen, China. Postcode: 518000 Tel: (86-0755) 8335 0911 8335 1011 8335 2011 8335 0611 Fax: (86-0755) 8335 9011

# Shanghai Fudan Microelectronics (HK) Ltd Taiwan Representative Office

Address: Unit 1225, 12F., No 252, Sec.1 Neihu Rd., Neihu Dist., Taipei City 114, Taiwan Tel : (886-2) 7721 1889 Fax: (886-2) 7722 3888

# Shanghai Fudan Microelectronics (HK) Ltd Singapore Representative Office

Address : 47 Kallang Pudding Road, #08-06,The Crescent @ Kallang ,Singapore 349318 Tel : (65) 6443 0860 Fax: (65) 6443 1215

#### Fudan Microelectronics (USA) Inc.

Address : 97 E Brokaw Road, Suite 320,San Jose,CA 95112 Tel : (+1)408-335-6936

#### Web Site: http://www.fmsh.com/

上海复旦微电子集团股份有限公司